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FDB024N06 N-Channel PowerTrench[®] MOSFET 60 V, 265 A, 2.4 m Ω

Features

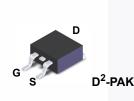
- $R_{DS(on)}$ = 1.8 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

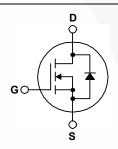
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Renewable System





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FDB024N06	Unit	
V _{DSS}	Drain to Source Voltage		60	V	
V _{GSS}	Gate to Source Voltage		±20	V	
ID		- Continuous (T _C = 25 ^o C, Silicon Limited)	265		
	Drain Current	- Continuous (T _C = 100 ^o C, Silicon Limited)	190		
		- Continuous (T _C = 25 ^o C, Package Limited)	120		
I _{DM}	Drain Current	- Pulsed (Note 1)	1060	А	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		2531	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns	
P _D	Power Dissingtion	(T _C = 25°C)	395	W	
	Power Dissipation	- Derate Above 25°C	2.6	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
ΤL	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for 5 Seconds	300	°C	

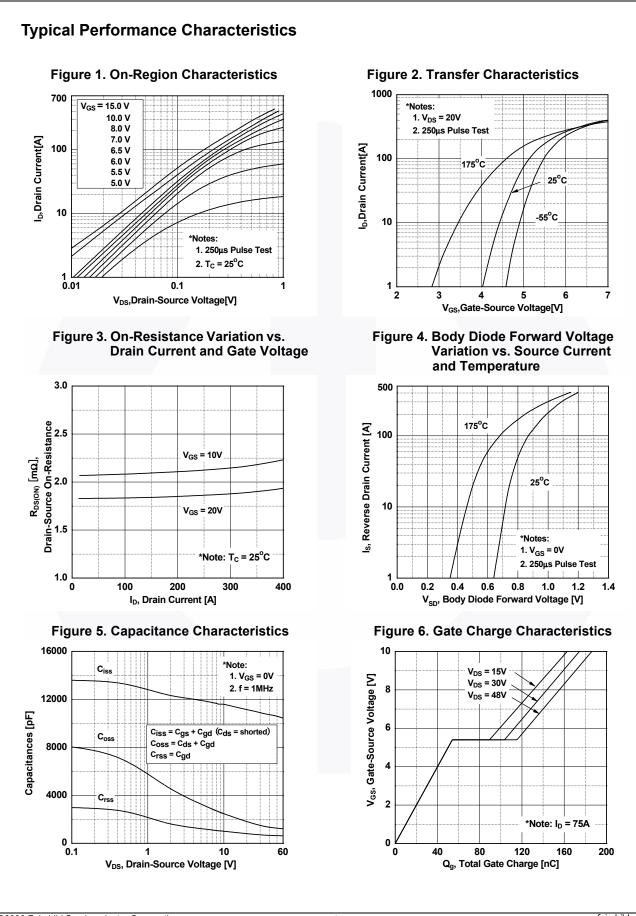
Thermal Characteristics

Symbol	Parameter	FDB024N06	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.38	
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient (1 in ² Pad of 2-oz Copper), Max.	40	

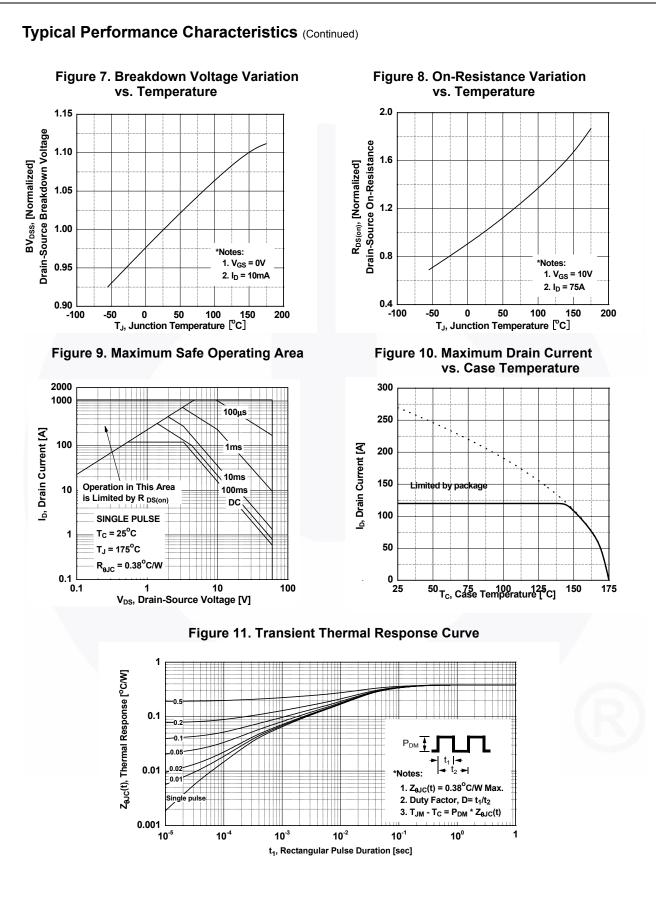
November 2013

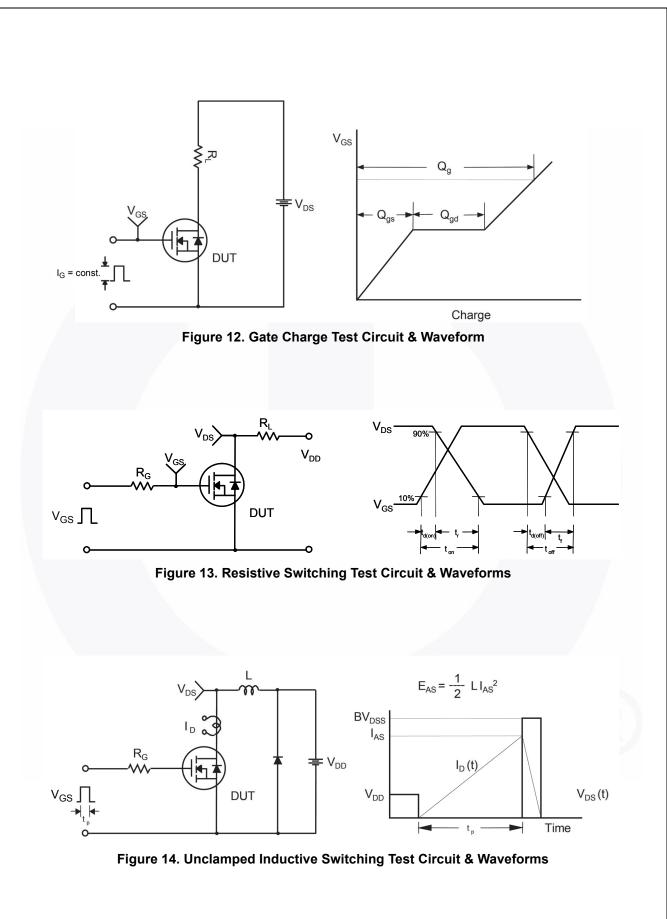
FDB024N06 —	
N-Channel Pow	
C	0
MOSFET	

Part Nur			Package	Packing Method	Reel Size	Тар	e Width	Qua	ntity
FDB024			D ² -PAK	Tape and Reel	330 mm	-	24 mm	800 units	
Electrica	l Char	racteristics T _c = 25 ^o	^o C unless o	therwise noted.					
Symbol		Parameter		Test Conditio	ons	Min.	Тур.	Max.	Unit
Off Charac	cteristic	S							
BV _{DSS}	Drain to	Source Breakdown Voltad	ae Ir	₀ = 250 μA, V _{GS} = 0 V	,	60	-	-	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient			$I_D = 250 \ \mu\text{A}$, Referenced to 25°C		-	0.04	-	V/ºC
I _{DSS}	Zero Ga	ate Voltage Drain Current		$V_{DS} = 60 V, V_{GS} = 0 V$ $V_{DS} = 60 V, V_{GS} = 0 V, T_{C} = 150^{\circ}C$ $V_{GS} = \pm 20 V, V_{DS} = 0 V$		-	-	1 500	μA
I _{GSS}	Gate to	Body Leakage Current				-	-	±100	nA
On Charac	teristic	S							
V _{GS(th)}		nreshold Voltage	V	ν _{GS} = V _{DS} , I _D = 250 μ/	4	2.5	3.5	4.5	V
R _{DS(on)}		Prain to Source On Resista		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 75 \text{ A}$		-	1.8	2.4	mΩ
9 _{FS}	Forwar	d Transconductance		$v_{\rm DS} = 10 \text{ V}, \text{ I}_{\rm D} = 75 \text{ A}$		-	200	-	S
Dynamic (Charact	eristics							
C _{iss}	Input C	apacitance			-	11190	14885	pF	
C _{oss}	Output	Capacitance		── V _{DS} = 25 V, V _{GS} = 0 V, ── f = 1 MHz		-	1610	2140	pF
C _{rss}	Reverse	e Transfer Capacitance	I			-	750	1125	pF
Q _{g(tot)}	Total G	ate Charge at 10V	V	/ _{DS} = 48 V, I _D = 75 A,	ь = 75 A	-	174	226	nC
Q _{gs}	Gate to	Source Gate Charge		$V_{\rm GS} = 10 \rm V$	-	-	54	-	nC
Q _{gd}		Drain "Miller" Charge		00	(Note 4)	-	50	-	nC
Switching	Charac	teristics			ļ				
-		n Delay Time					134	278	ns
t _{d(on)} t _r		n Rise Time	v	√ _{DD} = 30 V, I _D = 75 A,	-	324	658	ns	
		f Delay Time		$V_{GS} = 10 \text{ V}, \text{ R}_{G} = 25 \Omega$			348	706	ns
t _{d(off)}		f Fall Time		00 0	-		250	510	
t _f					(Note 4)	-	250	510	ns
		de Characteristics					I		
						-	-		A
						-			A
						-		1.3	V
								-	ns
Q _{rr}	Reverse	e Recovery Charge	u	$T_F/dl = 100 A/\mu s$		-	152	-	nC
2. L = 0.9 mH, I _{AS} 3. I _{SD} ≤ 75 A, di/di	Maximu Drain to Reverse Reverse g: pulse-width = 75 A, V _{DD} c ≤ 200 A/µs,	m Continuous Drain to Source m Pulsed Drain to Source Source Diode Forward Vo Recovery Time Recovery Charge h limited by maximum junction temp = 50 V, $R_G = 25 \Omega$, starting $T_J = 25$ $V_{DD} \le BV_{DSS}$, starting $T_J = 25^{\circ}C$. perating temperature typical charace	Diode Forw Itage V V d erature. °C.			-	- - 69 152	265 106 1.3 -	0



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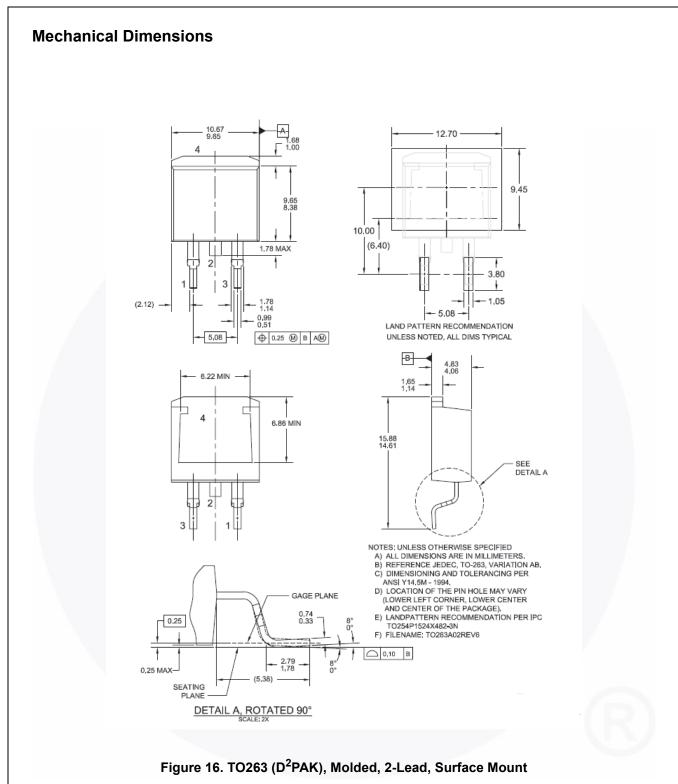




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DUT + V_{DS} a ۱_{SD} م L Driver R_G, Same Type as DUT L F ∨_{DD} $\prod V_{GS}$ • dv/dt controlled by R_{G} • I_{SD} controlled by pulse period Î Gate Pulse Width $\mathbf{V}_{\mathbf{GS}}$ D = Gate Pulse Period 10V (Driver) I_{FM}, Body Diode Forward Current I _{SD} di/dt (DUT) I_{RM} Body Diode Reverse Current V_{DS} (DUT) Body Diode Recovery dv/dt V_{SD} V_{DD} Body Diode Forward Voltage Drop Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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